

ABSTRACT OF THE DISCLOSURE

The invention provides a method for manufacturing a semiconductor device with which an impurity introduction region and a positioning mark region can be formed aligned, based on a common insulating film pattern. The method for manufacturing a semiconductor device includes an insulating film pattern formation step; a first photosensitive pattern formation step of forming, on the insulating film pattern, a first photosensitive pattern with an aperture that exposes a positioning mark region, the first photosensitive pattern covering an impurity introduction region; a level difference formation step of forming in the semiconductor substrate, at the aperture formed in the insulating film pattern, a level difference for adjusting a position of the photomask at the positioning mark region; a first photosensitive pattern removal step of removing the first photosensitive pattern; and an impurity introduction step of introducing the impurities through the aperture formed in the insulating film pattern into the impurity introduction region.